

HM6P5331

HM6P5331 – 2.0GHz/500MHz Dual Frequency Synthesizer

Features

- Full CMOS RF frequency synthesizer
- Low Current Consumption
- Selectable Powersave Mode
- Dual Modulus Prescaler
- Selectable Charge Pump High Z State
- 2.7V to 3.6V Operation
- Small Out Line 20 Pin TSSOP Package
24 Pin LGA(Leadless Grid Array) Package

Applications

- Portable Wireless Communications
- Cordless and Cellular Telephone Systems
- Wireless Local Area Networks(WLANs)
- Cable TV Tuners(CATV)
- Other Wireless Communication Systems

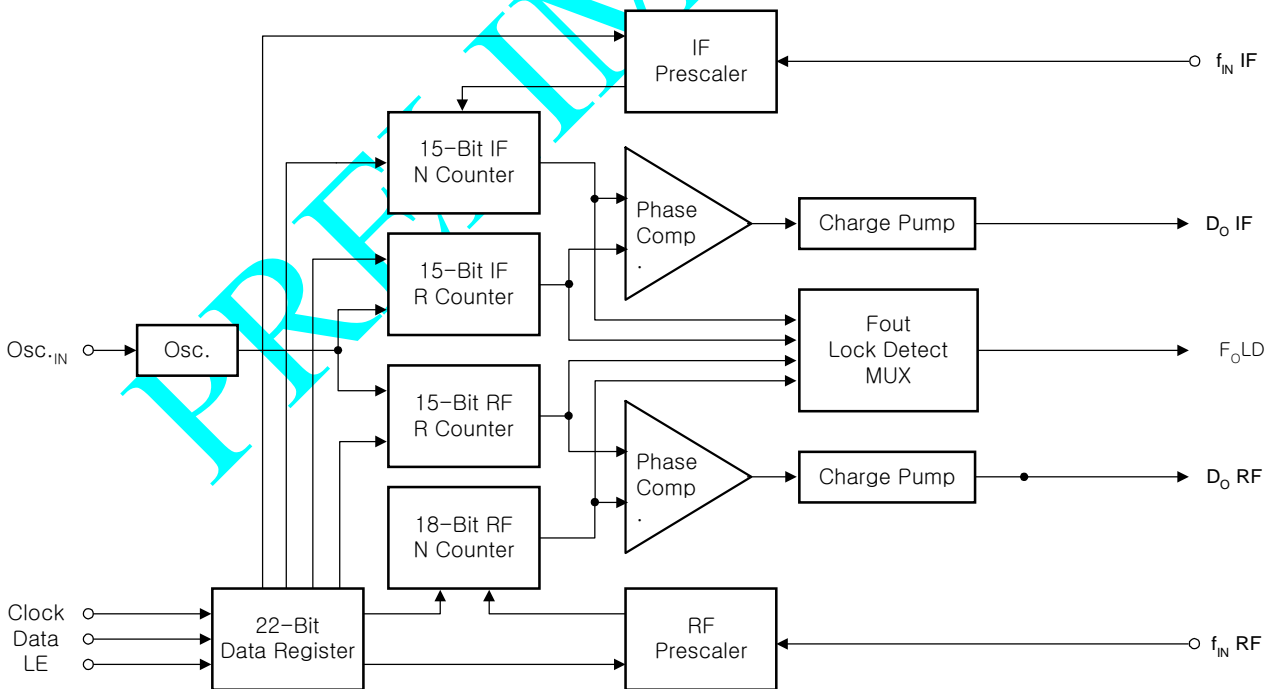
Description

The HM6P5331 of full CMOS monolithic, dual frequency synthesizer is to be used as a local oscillator for RF and IF of a dual conversion transceiver. It is fabricated using Hyundai's standard CMOS process.

HM6P5331 contains dual modulus prescalers. A 64/65 or a 128/129 prescaler can be selected for RF synthesizer and a 8/9 or 16/17 prescaler can be selected for IF synthesizer. Using digital phase locked loop technique, HM6P5331 provides the tuning voltage for voltage controlled oscillators to generate very stable low noise RF & IF local oscillator signals. Serial data is transferred into the HM6P5331 via three wire interface (Data, Enable, Clock). Supply voltage can range from 2.7 to 3.6 V. HM6P5331 features very low current consumption; 4.4mA at 3.0V.

HM6P5331 is available in a TSSOP 20-pin, LGA(Leadless Grid Array) 24-pin surface mount plastic package.

Functional Block Diagram

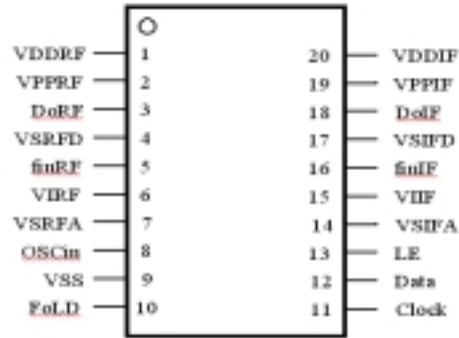


Pin Assignment

Pin Description

Leadless Grid Array Package

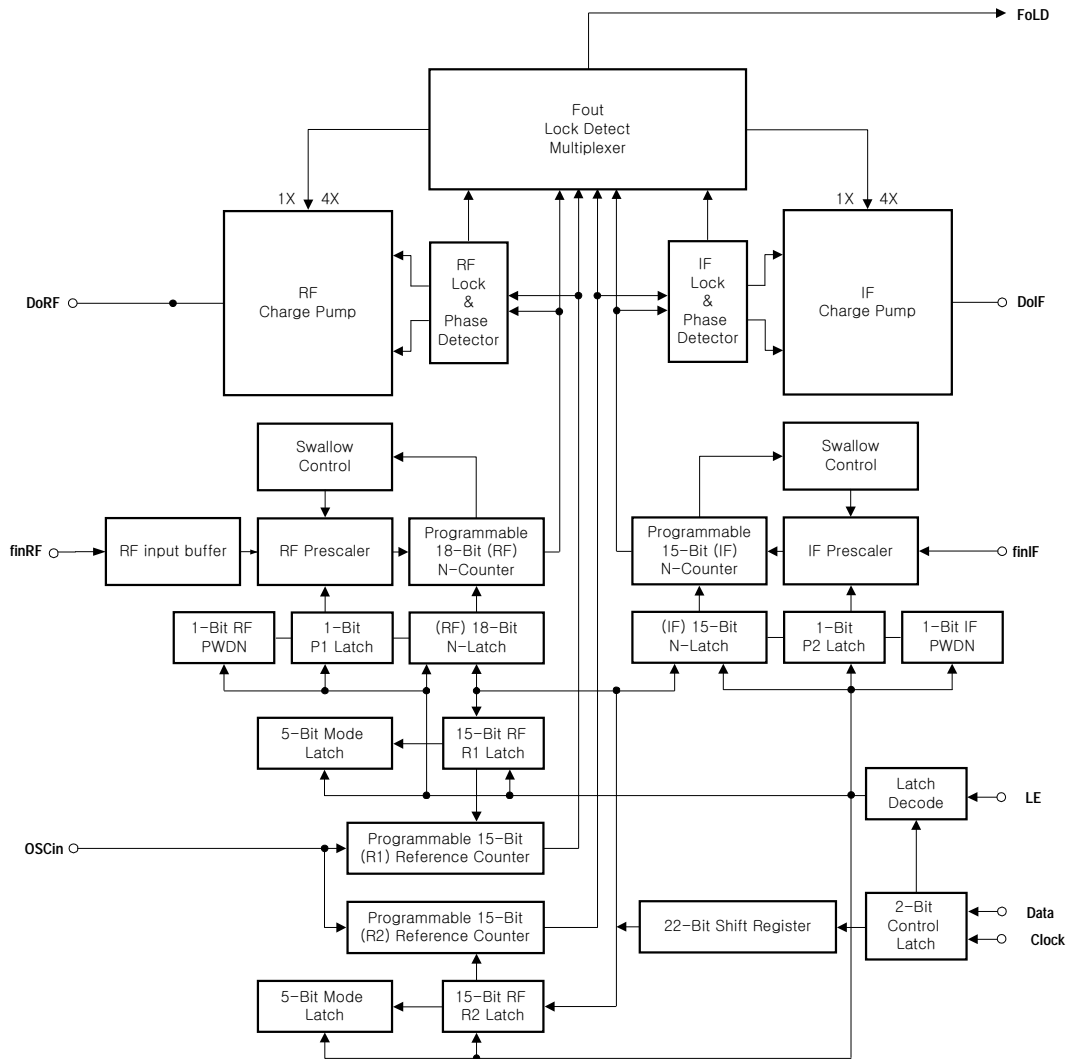
Thin Shrink Small Outline Package™



Pin No. HM6C5332 24-pin LGA Package	Pin No. HM6C5332 20-pin TSSOP Package	PIN NAME	I/O	Description
24	1	VDDRF	-	Power supply voltage input for RF analog and RF digital circuits. Input may range from 2.7V to 3.6V. VDDRF must equal VDDIF. Bypass capacitors should be placed as close as possible to this pin and be connected directly to the ground plane.
2	2	VPPRF	-	Power Supply for RF charge pump. Must be \geq VDDRF.
3	3	DoRF	O	Internal RF charge pump output. For connection to a loop filter for driving the input of an external VCO.
4	4	VSRFD	-	Ground for RF digital circuitry.
5	5	finRF	I	RF prescaler input. Small signal input from the VCO.
6	6	VIRF	-	This pin is to provide a bypass capacitor to the internal voltage supply and bypass capacitor must be placed between this pin and RF analog GND(Pin 7). With a slight performance degradation, this pin may be NC.
7	7	VSRFA	-	Ground for RF analog circuitry.
8	8	OSCin	I	Oscillator input. The input has a $VDDRF/2$ input threshold and can be driven from an external CMOS or TTL logic gate.
10	9	VSS	-	Ground for data interface, FoLD, and oscillator circuits.
11	10	FoLD	O	Multiplexed output of the RF/IF programmable or reference dividers, and RF/IF lock detect signals. CMOS output(See <i>Programmable Modes</i>)
12	11	Clock	I	High impedance CMOS Clock input. Data for the various counters is clocked in on the rising edge, into the 22-bit shift register.
14	12	Data	I	Binary serial data input. Data entered MSB first. The last two bits are the control bits. High impedance CMOS input.
15	13	LE	I	Load enable high impedance CMOS input. When LE goes HIGH, data stored in the shift register is loaded into one of the 4 appropriate latches(control bit dependent).

Pin No. HM6C5332 24-pin LGA Package	Pin No. HM6C5332 20-pin TSSOP Package	PIN NAME	I/O	Description
16	14	VSIFA	-	Ground for IF analog circuitry.
17	15	VIIF	-	This pin is to provide a bypass capacitor to the internal voltage supply and bypass capacitor must be placed between this pin and IF analog GND(Pin 14). With a slight performance degradation, this pin may be NC.
18	16	finIF	I	IF prescaler input. Small signal input from the VCO.
19	17	VSIFD	-	Ground for IF digital circuitry.
20	18	DoIF	O	Internal IF charge pump output. For connection to a loop filter for driving the input of an external VCO.
22	19	VPPIF	-	Power Supply for IF charge pump. Must be \geq VDDIF.
23	20	VDDIF	-	Power supply voltage input for IF analog, IF digital, data interface, FoLD, and oscillator circuits. Input may range from 2.7V to 3.6V. VDDIF must equal VDDRF. Bypass capacitors should be placed as close as possible to this pin and be connected directly to the ground plane.
1,9,13,21	X	NC	-	No Connect

Block Diagram



Absolute Maximum Ratings

Power Supply Voltage	
VDD	-0.3V to +4.2V
VPP	-0.3V to +4.2V
Voltage on Any Pin with GND = 0V (V _I)	-0.3V to +4.2V
Storage Temperature Range (T _S)	-65°C to +150°C
Lead Temperature (solder 4 sec.) (T _L)	260°C
Thermal Resistance(Typical) θ_{JA} (°C/W)	
TSSOP Package	130°C

Operating Conditions

Power Supply Voltage	
VDD	2.7V to 3.6V
VPP	VDD to 3.6V
Operating Temperature(T _A)	-40°C to 85°C

CAUTION: Stress above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. Other conditions above those indicated in the operational sections of this specification are not implied.

Electrical Characteristics $V_{DD} = 3.0V, -40^{\circ}C < T_A < 85^{\circ}C$, Except as Specified

Symbol	Parameter	Conditions	Min	Typ	Max	Units
I _{DD}	Power Supply Current	RF V _{DD} =2.7V to 3.6V, f _φ = 10KHz		3.2	5.4	mA
		IF V _{DD} =2.7V to 3.6V, f _φ = 10KHz		1.2		mA
I _{DD-PW_{DN}}	Powerdown Current	V _{DD} =3.0V		1	10	μA
f _{IN} RF	Operating Frequency		0.5	-	2.0	GHz
f _{IN} IF	Operating Frequency		50	-	500	MHz
f _{OSC}	Oscillator Frequency.		4	-	40	MHz
f _φ	Maximum Phase Detector Freq.		10	-	-	MHz
Pf _{IN} RF	RF Input Sensitivity	V _{DD} =2.7V to 3.6V	- 8.5	-	0	dBm
Pf _{IN} IF	IF Input Sensitivity	V _{DD} =2.7V to 3.6V	-10	-	0	dBm
V _{OSC}	Oscillator Sensitivity	OSC _{IN}	0.5	-	-	V _{PP}
V _{IH}	High Level Input Voltage	*	0.8 V _{DD}	-	-	V
V _{IL}	Low Level Input Voltage	*	-	-	0.2 V _{DD}	V
I _{IH}	High Level Input Current	V _{IH} =V _{DD} =3.6V*	-1.0	-	1.0	μA
I _{IL}	Low Level Input Current	V _{IL} =0V, V _{DD} =3.6V*	-1.0	-	1.0	μA
I _{IH}	Oscillator Input Current	V _{IH} =V _{DD} =3.6V	-	-	100	μA
I _{IL}	Oscillator Input Current	V _{IL} =0V, V _{DD} =3.6V	-100	-	-	μA
V _{OH}	High-Level Output Voltage	I _{OH} = -500 μA	V _{DD} -0.4	-	-	V
V _{OL}	Low-Level Output Voltage	I _{OL} = 500 μA	-	-	0.4	V
t _{CS}	Data Clock Setup Time	See Data Input Timing	50	-	-	ns
t _{CH}	Data Clock Hold Time	See Data Input Timing	10	-	-	ns
t _{CWH}	Clock Pulse Width High	See Data Input Timing	50	-	-	ns
t _{CWL}	Clock Pulse Width Low	See Data Input Timing	50	-	-	ns
t _{ES}	Clock to Load Enable Setup Time	See Data Input Timing	50	-	-	ns
t _{EW}	Load Enable Pulse Width	See Data Input Timing	50	-	-	ns

* Clock, Data and LE. Does not include f_{IN}RF, f_{IN}IF and OSC_{IN}.

Programmable Modes

Several modes of operation can be programmed with bits R16-R18 including the phase detector polarity and charge pump High Z State. The prescaler and powerdown modes are selected with bits N19 and N20. The programmable modes and truth table for the programmable modes are shown below.

C1	C2	R16	R17	R18	R19	R20
0	0	IF Phase Detector Polarity	IF I _{CPO}	IF D _o High Z	IF LD	IF F _o
0	1	RF Phase Detector Polarity	RF I _{CPO}	RF D _o High Z	RF LD	RF F _o
1	0	-	-	-	IF Prescaler	Powerdown IF
1	1	-	-	-	RF Prescaler	Powerdown RF

Mode Select Truth Table

	PHASE DETECTOR POLARITY	D _o High Z STATE	I _{CPO} (NOTE 1)	IF PRESCALER	RF PRESCALER	POWERDOWN (NOTE 2)
0	Negative	Normal Operation	LOW	8/9	64/65	Powered Up
1	Positive	High Z State	HIGH	16/17	128/129	Powered Down

NOTES:

1. Activation of the IF PLL or RF PLL powerdown modes result in the disabling of the respective N counter divider and debiasing of its respective f_{IN} inputs (to a high impedance state). Powerdown forces the respective charge pump and phase comparator logic to a High Z State condition. The R counter functionality does not become disabled until both IF and RF powerdown bits are activated. The OSC_{IN} pin reverts to a high impedance state when this condition exists. The control register remains active and capable of loading and latching in data during all the powerdown modes.

F_o LD (Pin 10) Output Truth Table

RF R[19] (RF LD)	IF R[19] (IF LD)	RF R[20] (RF F _o)	IF R[20] (IF F _o)	F _o OUTPUT STATE
0	0	0	0	Disabled (Note1)
0	1	0	0	IF Lock Detect (Note2)
1	0	0	0	RF Lock Detect (Note2)
1	1	0	0	RF/IF Lock Detect (Note2)
X	0	0	1	IF Reference Divider Output
X	0	1	0	RF Reference Divider Output
X	1	0	1	IF Programmable Divider Output
X	1	1	0	RF Programmable Divider Output
0	0	1	1	For Internal Use Only
0	1	1	1	For Internal Use Only
1	0	1	1	For Internal Use Only
1	1	1	1	Counter Reset (Note4)

X = don't care condition

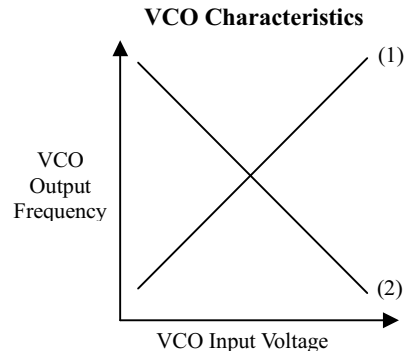
NOTES:

1. When the F_o LD output is disabled, it is actively pulled to a low logic state.
2. Lock detect output provided to indicate when the VCO frequency is in "lock". When the loop is locked and a lock detect mode is selected, the pins output is HIGH, with narrow pulse LOW. In the RF/IF lock detect mode a locked condition is indicated when RF and IF are both locked.
3. The Counter Reset mode bits R19 and R20 when activated reset all counters. Upon removal of the Reset bits then N counter resumes counting in "close" alignment with the R counter. (The maximum error is one prescaler cycle). If the Reset bits are activated the R counter is also forced to Reset, allowing smooth acquisition upon powering up.

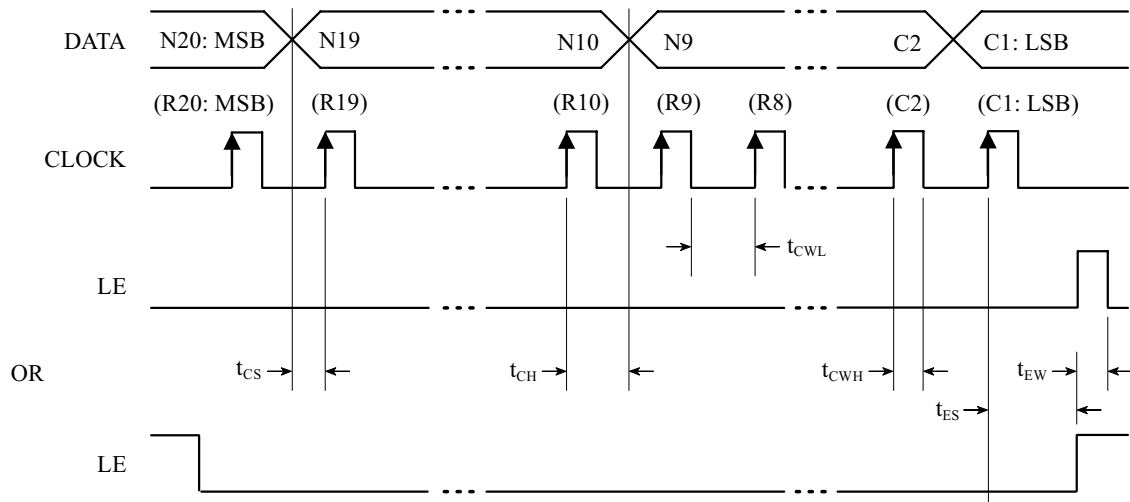
Phase Detector Polarity

Depending upon VCO characteristics, R16 bit should be set accordingly:

When VCO characteristics are positive like (1), R16 should be set HIGH; When VCO characteristics are negative like (2), R16 should be set LOW.



Serial Data Input Timing

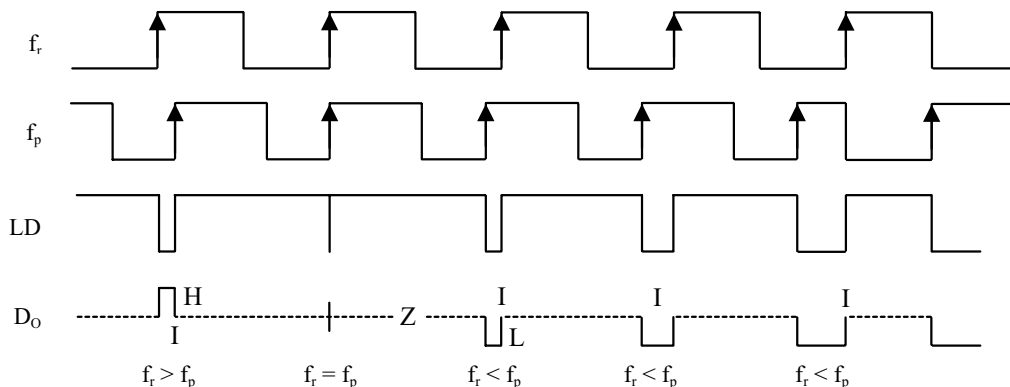


NOTES:

1. Parenthesis data indicates programmable reference divider data.
2. Data shifted into register on clock rising edge.
3. Data is shifted in MSB first.

Test Conditions: The Serial Data Input Timing is tested using a symmetrical waveform around $V_{DD}/2$. The test waveform has an edge rate of 0.6V/ns with amplitudes of 2.2V at $V_{DD} = 2.7V$ and 2.6V at $V_{DD} = 3.6V$.

Phase Comparator and Internal Charge Pump Characteristics



NOTES:

1. Phase difference detection range: -2π to $+2\pi$
2. The minimum width pump up and pump down current pulse occur at the D_o pin when the loop is locked.
3. R16 = HIGH

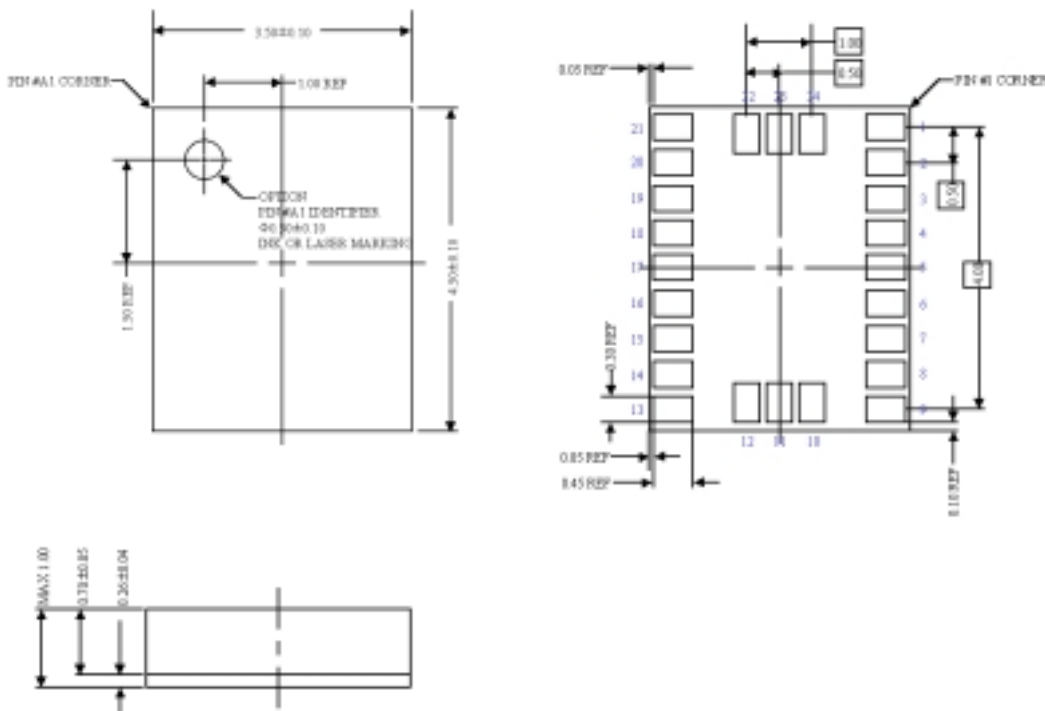
Powerdown Operation

Synchronous and asynchronous powerdown modes are both available. Synchronously powerdown occurs if the respective loop's R18 bit (Do High Z State) is LOW when its N20 bit (Powerdown) becomes HI. Asynchronous powerdown occurs if the loop's R18 bit is HI when its N20 bit becomes HI. In the synchronous powerdown mode, the powerdown function is gated by the charge pump to prevent unwanted frequency jumps. Once the powerdown program bit N20 is loaded, the part will go into powerdown mode when the charge pump reaches a High Z condition. In the asynchronous powerdown mode, the device powers down immediately after the LE pin latches in a HI condition on the powerdown bit N20. Activation of either the IF or RF PLL powerdown conditions in either synchronous or asynchronous modes forces the respective loop's R and N dividers to their load state condition and debiasing of its respective fin input to a high impedance state. The oscillator circuitry function does not become disabled until both IF and RF powerdown bits are activated. The control register remains active and capable of loading and latching data during all of the powerdown modes. The device returns to an actively powered up condition in either synchronous or asynchronous modes immediately upon LE latching LOW data into bit N20.

Powerdown Mode Select Table

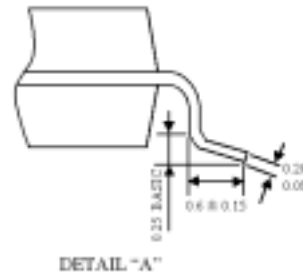
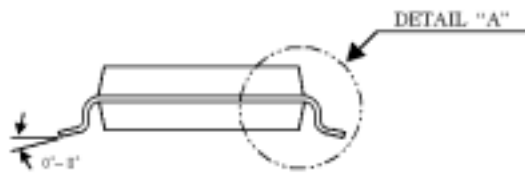
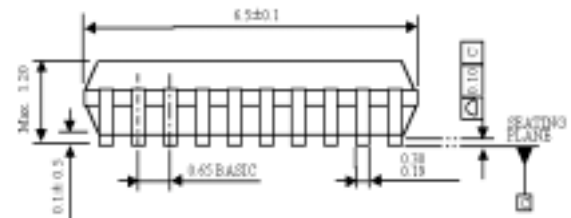
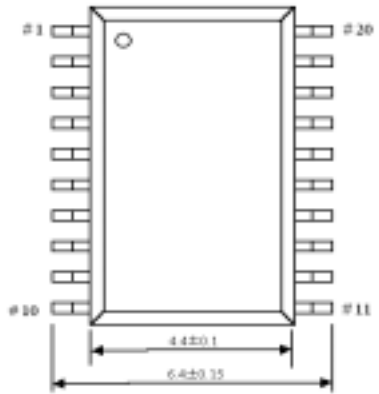
R18	N20	Powerdown Status
0	0	PLL Active
1	0	PLL Active (Charge Pump High Z State)
0	1	Synchronous Powerdown Initiated
1	1	Asynchronous Powerdown Initiated

Physical Dimensions (unit : mm)



Leadless Grid Array Package

Physical Dimensions continued (unit : mm)



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